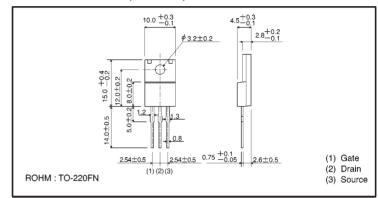
Switching (600V, 7A) 25K2740

Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Wide SOA (safe operating area).
- 4) Gate-source voltage (Vgss) guaranteed to be ± 30 V.
- 5) Easily designed drive circuits.
- 6) Easy to parallel.

●Structure Silicon N-channel MOSFET

External dimensions (Units: mm)



●Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		Voss	600	V
Gate-source voltage		Vgss	±30	V
Drain current	Continuous	lo	7	Α
	Pulsed	lop*	28	Α
Reverse drain current	Continuous	IDR	7	Α
	Pulsed	ldrp*	28	Α
Total power dissipation(Tc=25°C)		P□	30	W
Channel temperature		Tch	150	°C
Storage temperature		Tstg	-55~ + 150	°C

^{*} Pw≦10 μs, Duty cycle≦1%

Packaging specifications

	Package	Bulk
Туре	Code	_
	Basic ordering unit (pieces)	500
2SK2740		0

Transistors 2SK2740

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Gate-source leakage	lgss	_	_	±100	nA	V _{GS} =±30V, V _{DS} =0V
Drain-source breakdown voltage	V(BR)DSS	600	_	_	٧	ID=1mA, VGS=0V
Zero gate voltage drain current	loss	_	_	100	μΑ	V _{DS} =600V, V _{GS} =0V
Gate threshold voltage	VGS(th)	2.0	_	4.0	٧	V _{DS} =10V, I _D =1mA
Static drain-source on-state resistance	RDS(on)	_	1.0	1.2	Ω	In=4A, VGS=10V
Forward transfer admittance	Yfs *	3.0	6.0	_	S	In=4A, Vns=10V
Input capacitance	Ciss	_	1050	_	pF	V _{DS} =10V
Output capacitance	Coss	_	210	_	pF	V _{GS} =0V
Reverse transfer capacitance	Crss	_	80	_	pF	f=1MHz
Turn-on delay time	td(on)	_	19	_	ns	ID=4A, VDD≒150V
Rise time	tr	_	22	_	ns	V _{GS} =10V
Turn-off delay time	td(off)	_	79	_	ns	RL=37.5Ω
Fall time	tf	_	30	_	ns	R _G =10Ω
Reverse recovery time	trr	_	590	_	ns	IDR=7A, VGS=0V
Reverse recovery charge	Qrr	_	4.6	_	μC	di/dt=100A/ μs

^{*} Pw \leq 300 μ s, Duty cycle \leq 1%

Electrical characteristic curves

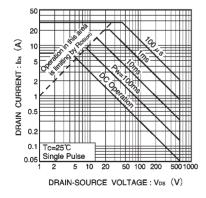


Fig.1 Maximum safe operating area

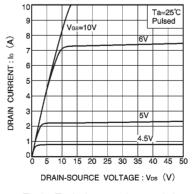


Fig.2 Typical output characteristics

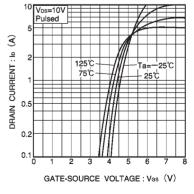


Fig.3 Typical transfer characteristics

Transistors 2SK2740

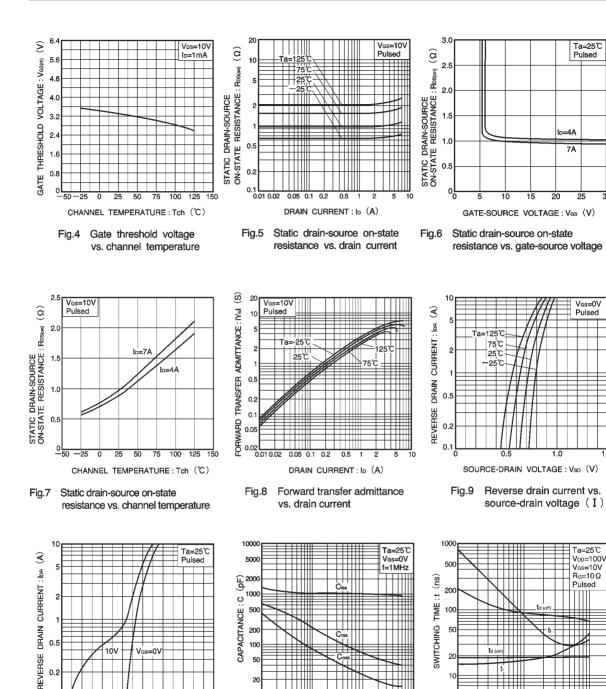


Fig.10 Reverse drain current vs. source-drain voltage (I)

SOURCE-DRAIN VOLTAGE: Vsp (V)

1.0

1.5

0.5

Fig.11 Typical capacitance vs. drain-source voltage

DRAIN-SOURCE VOLTAGE: VDs (V)

50 100 200

Fig.12 Switching characteristics (See Figures 16 and 17 for the measurement circuit and resultant waveforms)

DRAIN CURRENT: lo (A)

0.2

0.1 L

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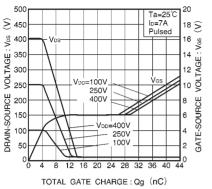


Fig.13 Dynamic input characteristics (See Figure 18 for measurement circuit)

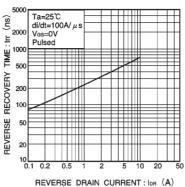


Fig.14 Reverse recovery time vs. reverse drain current

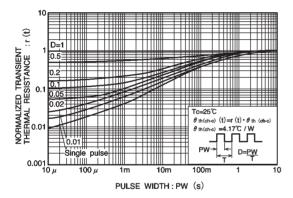
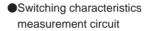


Fig.15 Normalized transient thermal resistance vs. pulse width



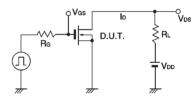


Fig.16 Switching time measurement circuit

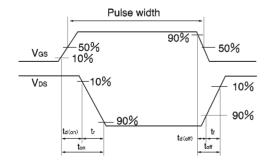


Fig.17 Switching time waveforms

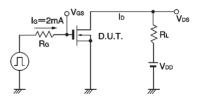


Fig.18 Gate charge measurement circuit



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